

#### Features

- Low Forward Voltage (V<sub>F</sub>) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior

## Applications

- Battery Chargers
- Solar & Renewable Energy Power Conversion
- Industrial Power Supplies
- Boost Diodes in PFC & DC-DC





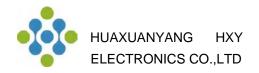




Part Number	Package	Marking
HC4D30120H	TO247-2L	HC4D30120H

#### **Maximum Ratings**( $T = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Value	Unit	Test Conditions	Note	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	1200	V			
DC Blocking Voltage	V <sub>DC</sub>	1200	V			
	I <sub>F</sub>	94	A	T <sub>J</sub> = 25 °C		
Continuous Forward Current		45		T <sub>J</sub> = 135 °C	Fig. 3	
		30		T <sub>J</sub> = 155 °C		
Repetitive Peak Forward Surge	I <sub>FRM</sub>	121		$T_c = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{Half Sine Pulse}$		
Current		68		$T_c = 110 \text{ °C}, t_p = 10 \text{ ms}, \text{Half Sine Pulse}$		
Non-Repetitive Forward Surge		233		$T_c = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{Half Sine Pulse}$		
Current	FSM	209		$T_c = 110 \text{ °C}, t_p = 10 \text{ ms}, \text{Half Sine Pulse}$		
Power Dissipation	P <sub>tot</sub>	441	W	$T_c = 25 \text{ °C}$	- Fig. 4	
		191		$T_c = 110 \text{ °C}$		
i²t Value	∫i²t	271	A <sup>2</sup> s	$T_{c} = 25 \text{ °C}, t_{p} = 10 \text{ ms}$		
		218		$T_c = 110 \text{ °C}, t_p = 10 \text{ ms}$		



#### **Electrical Characteristics**

Parameter	Symbol	Тур.	Max.	Units	Test Conditions	Note	
Forward Voltage	M	1.5	1.8	V	I <sub>F</sub> = 30 A, T <sub>J</sub> = 25 °C	Fig. 1	
	V <sub>F</sub>	2.2	3		I <sub>F</sub> = 30 A, T <sub>J</sub> = 175 °C	Fig. 1	
Reverse Current		40	250		V <sub>R</sub> = 1200 V, T <sub>J</sub> = 25 °C		
	R	70	450	μA	V <sub>R</sub> = 1200 V, T <sub>J</sub> = 175 °C	Fig. 2	
Total Capacitive Charge	Q <sub>c</sub>	152		nC	$V_{R} = 800 \text{ V}, T_{J} = 25 \text{ °C}$	Fig. 5	
		2,177		pF	$V_{R} = 0 V, T_{J} = 25 °C, f = 1 MHz$		
Total Capacitance	С	136			$V_{R} = 400 \text{ V}, \text{ T}_{J} = 25 \text{ °C}, \text{ f} = 1 \text{ MHz}$	Fig. 6	
		100			$V_{R} = 800 \text{ V}, \text{ T}_{J} = 25 \text{ °C}, \text{ f} = 1 \text{ MHz}$		
Capacitance Stored Energy	E <sub>c</sub>	44		μJ	V <sub>R</sub> =800 V	Fig. 7	

Note:

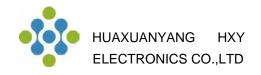
SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

## **Thermal & Mechanical Characteristics**

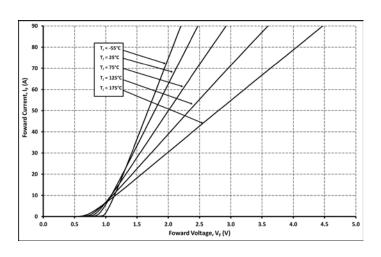
Parameter	Symbol	Value	Units	Note
Thermal Resistance, Junction to Case (Typ.)	R <sub>θ, JC</sub>	0.34	°C / W	
Operating Junction & Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	Fig. 8
Maximum Processing Temperature	T <sub>PROC</sub>	325		10 min. Maximum

## **Electrostatic Discharge (ESD) Classifications**

Parameter	Symbol	Value
Human Body Model	НВМ	Class 3B (≥ 8000 V)
Charge Device Model	CDM	Class C3 (≥ 1000 V)

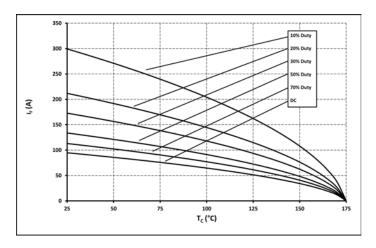


## **Typical Performance**



**Figure 1. Forward Characteristics** 

**Figure 3. Current Derating** 





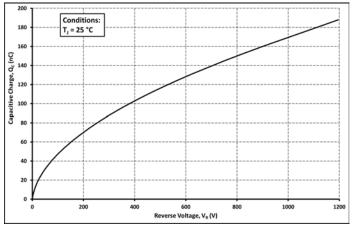
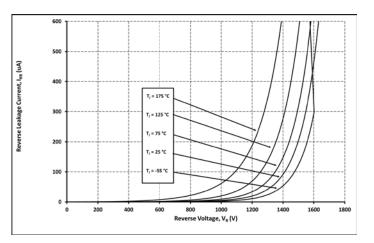


Figure 2. Reverse Characteristics



**Figure 4. Power Derating** 

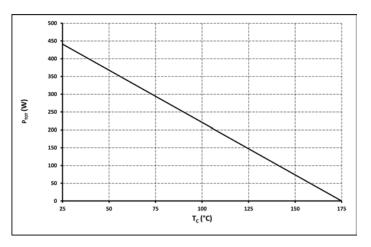
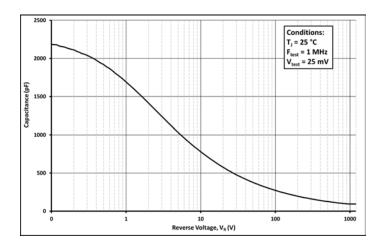
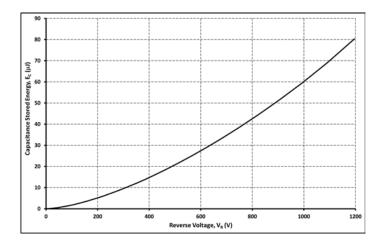


Figure 6. Capacitance vs. Reverse Voltage

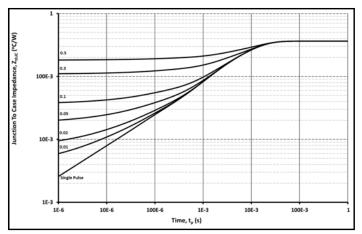




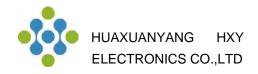
## **Typical Performance**



# Figure 7. Capacitance Stored Energy



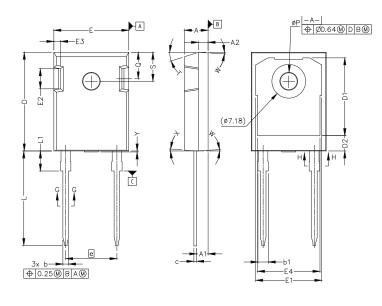
# Figure 8. Transient Thermal Impedance



## **Package Dimensions**

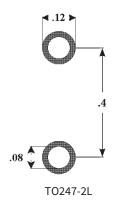
Package: TO247-2L

All dimensions in mm.

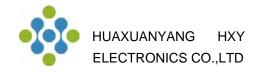


	MILLIM	FTERS	INCH	FS		
SYM	MIN	MAX	MIN	MAX		
А	4.83	5.21	.190	.205		
Al	2.29	2.54	.090	.100		
A2	1.91	2.16	.075	.085		
b'	1.07	1.28	.042	.050		
b	1.07	1.33	.042	.052		
b1	1.91	2.41	.075	.095		
b2	1.91	2.16	.075	.085		
c'	0.55	0.65	.022	.026		
с	0.55	0.68	.022	.027		
D	20.80	21.10	.819	.831		
D1	16.25	17.35	.640	.683		
D2	2.86	3.16	.112	.124		
Е	15.75	16.13	.620	.635		
E1	13.10	14.15	.516	.557		
E2	3.68	5.10	.145	.201		
E3	1.00	1.90	.039	.075		
E4	12.38	13.43	.487	.529		
e	10.88	BSC	.428 BS	SC		
L	19.81	20.32	.780	.800		
L1	4.10	4.40	.161	.173		
ØР	3.51	3.65	.138	.144		
0	5.49	6.00	.216	.236		
S	6.04	6.30	.238	.248		
Т		17.5° REF.				
W		3.5° RE	EF.			
Х		4° REF.				
Y	0	0.50	0	0.020		

**Recommended Solder Pad Layout** 



all units are in inches



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